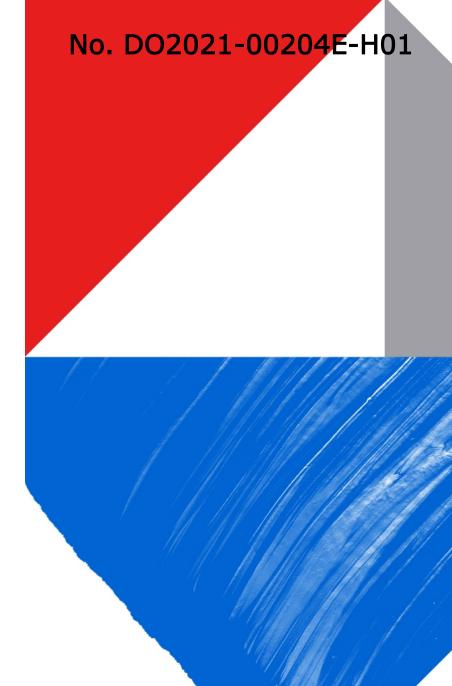
#### Change of Assembly material

#### **TOSHIBA**

Nov. 9, 2022 Quality & Reliability group I ,Oita Office Semiconductor quality & reliability engineering department(dept.) Toshiba Electronic Devices & Storage Corporation



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### Change Overview



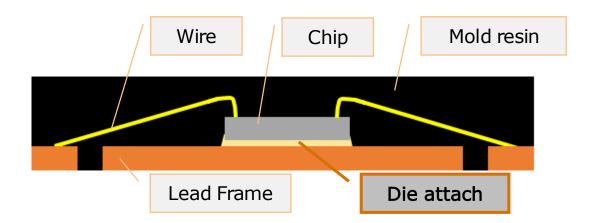
## **1** Change Overview

#### ■Background/reason

Due to the discontinuation of production, We will change the die attach material of the assembly material. The die attach material to be change is from the same manufacturer, and we have a track record of mass production.

We ask for approval by January 2023.

In addition, since the IC standard does not change, it can be use in the same way as conventional products.



Package cross section schematic



Change Point



## Change Point 5M1E

	5M1E	Change point	Presence or absence of change	Remark
Θ	Man	_	No	
⊜	Machine	_	No	
۲	Material	Die attach (A→B)	Yes	A and B are the same manufacturer and have a track record of mass production.
4	Method	Connection conditions for new Die attach	Yes	
5	Measurement	_	No	
6	Environment	_	No	

## 2 Change Point Detailed description

#### ■About material Die attach

		Туре	Maker	Principal component		
А	Current	Epoxy silver paste	S	<ul> <li>Silver</li> <li>Modified epoxy re</li> <li>Other</li> </ul>	(filler) esin (Main agent) (Hardener , etc)	
В	New	Acrylic silver paste	S	<ul> <li>Silver</li> <li>Acrylic resin</li> <li>Other</li> </ul>	(filler) (Main agent) (Hardener , etc)	

#### Products

Please refer to the attached sheet.

**Risk Analysis** 



# **3** Risk Analysis

#### DRBFM

No	Parts /	Change Point	Function	Failure Mode	Failure Cause	Effect of Failure	Item to be feflected on	Counterm easure Rusult
	Process					Fallure	evaluation	Rusurt
1	Dice Bond	•Paste Material •from Epoxy silver paste to Acrylic silver paste	•Stick Chip to Lead frame •Transfer the heat generated from Chip to Die pad	Insufficient wetness of Paste	The discharge rate is small because the manufacturing conditions do not match the material characteristics.	Perform ance degradation	Paste wettability	
				Large amount of Paste creeps up	Large discharge rate because the manufacturing conditions do not match the material characteristics.	Malfunction	Paste craw up	
				The Paste thickness is thin	The discharge rate is small because the manufacturing conditions do not match the material characteristics.	•Yield decline •performance degradation	Paste thickness	
				Thick Paste	Large discharge rate because the manufacturing conditions do not match the material characteristics.	Yield decline	Paste thickness	
				Chip decrease in	Insufficient wetness of Paste	Yield decline	Die share strength	
				adhesive strength	The Paste thickness is thin	Decreased reliability	Reliability test (Temperature Cycling)	page 10 onwards please refer
				Delamination on the back side of Chip	Since the amount of Paste material discharged is small, the adhesive strength between Chip and Lead frame's die pad decreases, and delamination occurs due to thermal stress etc.	Decreased reliability	Reliability test (Temperature Cycling)	
					Due to material properties , the stress when heat is applied increases and delamination occurs.	Decreased reliability	Reliability test (Temperature Cycling)	
					Moisure in the package avaporates due to the heat during reflow , and delamination occurs at that pressure.	Decreased reliability	Reliability test (MRT)	
				Decrease in wire	Material properties spoil	Malfunction	Wire bond strength	
				bond strength Reduced heat	US/load Decrease in the thermal		Thermal resistance	
				dissipation	conductivity	Product malfunction	Transient heat transfer	

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## **3 Risk Analysis** Extraction of evaluation items

		Item	Condition	Criteria		
	Die attach	Paste wettability	_	Process capability >1.33		
Jance		Paste crawl up	_	Process capability >1.33		
Assembly performance		Paste thickness	_	Process capability >1.33		
nbly p		Die share strength	—	Process capability >1.33		
Asser	Wire bond	Wire bond share strength	—	Process capability >1.33		
		Wire bond pull strength	—	Process capability >1.33		
Reliability test		MRT (Pre Condition)	Bake(125°C/24h)+Moisture Soak(30°C/60%/192h) Reflow260°C3times	No Delamination		
Reliat	Te	emperature Cycling	Pre Condition + -65~150°C 300cyc	No electrical characteristics failure		
[		rmal resistance sient heat transfer	sim.	No significant different between before and after change		

## **Evaluation Result**



■Concept of evaluation representative product

Die attachability , Reliability test

Representative product⊝ : Die size / Package size maximum Representative product⊜ : Die size / Package size minimum



•Wire bondability

Representative product  $\circledast$  : Wire type ~ Gold (minimum diameter)

Representative product (4) : Wire type ~ Copper (maximum diameter)

		Item	Criteria	Result(sample size)			
ance		Paste wettability	Process capability >1.33	Product⊝ : All100%(n=6pcs) Product⊜ : All100%(n=17pcs)			
	Die attach	Paste crawl up	Process capability >1.33	Product $\ominus$ : Process capability =2.21(n=6pcs) Product $\ominus$ : Process capability =3.04(n=17pcs)			
erform	Die a	Paste thickness	Process capability >1.33	Product $\ominus$ : Process capability =2.21(n=6pcs) Product $\ominus$ : Process capability =3.04(n=17pcs)			
Assembly performance		Die share strength	Process capability >1.33	Product⊖ : Process capability =8.05(n=6pcs) Product⊜ : Process capability =3.83(n=17pcs)			
Asser	Wire bond	Wire bond share strength	Process capability >1.33	Product $\circledast$ : Process capability =5.97(n=30wire) Product (4) : Process capability =5.02(n=30wire)			
		Wire bond pull strength	Process capability >1.33	Product⊛ : Process capability =2.91(n=30wire) Product④ : Process capability =2.99(n=30wire)			
Reliability test	Pre Condition		No Delamination	Product⊝ : 22/22pcs OK Product⊜ : 22/22pcs OK			
	Tem	perature Cycling	No electrical characteristics failure	Product⊝ : 22/22pcs OK Product⊜ : 22/22pcs OK			

#### There are no defects and no problems.

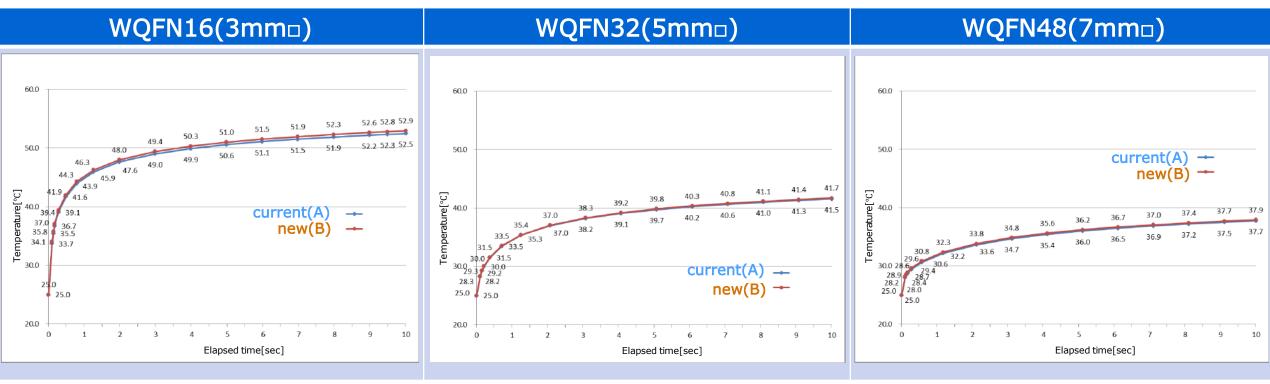
■Thermal resistance(sim. result)

Substrate specification : D74-1.6t-4 layers FR-4 substrates Mounting solder : Sn-3.0Ag-0.5Cu Exposed die pad connection : Yes Power consumption : 1.0[W]

Package			W QFN16	(3mm□)	W QFN32(5mm□)		W QFN48(7mm□)	
Die size			1.53 X 1.44 X 0.20		2.84 x 2.63 x 0.20		2.20 x 2.20 x 0.20	
W et area (Model)			Several and a several		State		The second secon	
Die attach material			Current(A)	New(B)	Current(A)	New(B)	Current(A)	New(B)
Fever state		55 52,857 50,714 48,571 44,226 42,143 40 37,857 35,714 40 33,7857 31,429 29,286 27,143 25						
Junction temp.	: Tj	[°C]	66.45	66.90	55.37	55.52	51.44	51.62
Ambient temp.	: Ta	[°C]	25.00	25.00	25.00	25.00	25.00	25.00
Case surface temp.	: Tc1	[°C]	66.05	66.47	55.24	55.38	51.29	51.46
Therm al resistance	: <del>(</del> ја	[°C/W]	41.45	41.90	30.37	30.52	26.44	26.62
Thermal resistance	: Øc	[°C/W]	0.40	0.43	0.13	0.14	0.15	0.16
Allowable loss		[W]	2.41	2.39	3.29	3.28	3.78	3.76

Transient electro thermal comparison(sim. result)

Time to calculate : 0~10[sec] Measurement position : Above die Power consumption : 1.0[W]



#### Analysis results are equivalent regardless of package size.

### Changeover Schedule



### **5** Changeover schedule



Since the expiration date of the current material is until March 2023, We would appreciate by the end of January 2023.



#### The END

